Dual Fully-Silicided Gate MOSFETs

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a plurality of silicidation steps is provided. In the preferred embodiment in which the semiconductor device is a MOSFET, the source/drain regions are silicided. A dielectric layer is formed and the etch stop layer is removed from the gate electrode of the MOSFET. A second silicidation process is performed to silicide the gate electrode. The process may be performed individually for each transistor, allowing the electrical characteristics of each transistor to be determined individually.